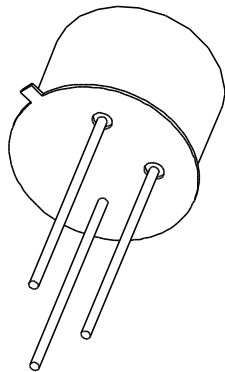


# DATA SHEET



## **BFX85** NPN switching transistor

Product specification  
Supersedes data of September 1994  
File under Discrete Semiconductors, SC04

1997 Apr 22

## NPN switching transistor

BFX85

## FEATURES

- High current (max. 1 A)
- Low voltage (max. 60 V).

## APPLICATIONS

- General purpose switching and amplification
- Industrial applications.

## DESCRIPTION

NPN transistor in a TO-39 metal package.

## PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	collector, connected to case

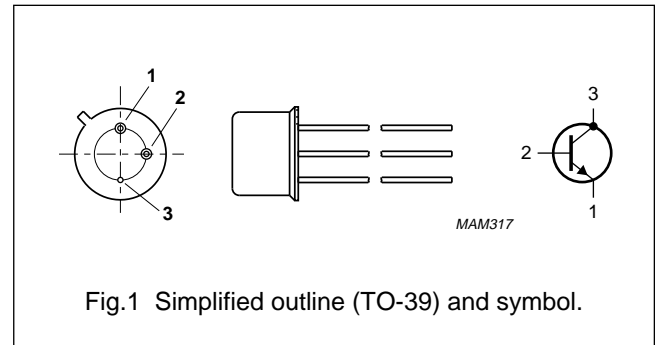


Fig.1 Simplified outline (TO-39) and symbol.

## QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{CB0}$	collector-base voltage	open emitter	–	–	100	V
$V_{CEO}$	collector-emitter voltage	open base	–	–	60	V
$I_C$	collector current (DC)		–	–	1	A
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$	–	–	800	mW
		$T_{case} \leq 100\text{ °C}$	–	–	2.86	W
$h_{FE}$	DC current gain	$I_C = 150\text{ mA}; V_{CE} = 10\text{ V}$	70	142	–	
$f_T$	transition frequency	$I_C = 50\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	50	–	–	MHz
$t_{off}$	turn-off time	$I_{Con} = 150\text{ mA}; I_{Bon} = 15\text{ mA}; I_{Boff} = -15\text{ mA}$	–	360	–	ns

## NPN switching transistor

BFX85

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	100	V
$V_{CEO}$	collector-emitter voltage	open base	–	60	V
$V_{EBO}$	emitter-base voltage	open collector	–	6	V
$I_C$	collector current (DC)		–	1	A
$I_{CM}$	peak collector current		–	1	A
$I_{BM}$	peak base current		–	100	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$	–	800	mW
		$T_{case} \leq 25\text{ °C}$	–	5	W
		$25\text{ °C} \leq T_{case} \leq 100\text{ °C}$	–	2.86	W
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	175	°C
$T_{amb}$	operating ambient temperature		–65	+150	°C

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	in free air	200	K/W
$R_{th\ j-c}$	thermal resistance from junction to case		35	K/W

## NPN switching transistor

## BFX85

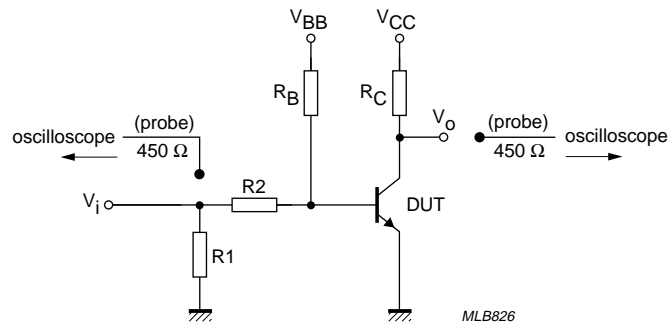
## CHARACTERISTICS

$T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CBO}$	collector cut-off current	$I_E = 0; V_{CB} = 80\text{ V}$	–	2	50	nA
		$I_E = 0; V_{CB} = 80\text{ V}; T_j = 100\text{ }^\circ\text{C}$	–	0.1	2.5	$\mu\text{A}$
		$I_E = 0; V_{CB} = 100\text{ V}$	–	10	500	nA
		$I_E = 0; V_{CB} = 100\text{ V}; T_j = 100\text{ }^\circ\text{C}$	–	0.5	30	$\mu\text{A}$
$I_{EBO}$	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	2	50	nA
		$I_C = 0; V_{EB} = 5\text{ V}; T_j = 100\text{ }^\circ\text{C}$	–	0.1	2.5	$\mu\text{A}$
		$I_C = 0; V_{EB} = 6\text{ V}$	–	10	500	nA
$h_{FE}$	DC current gain	$I_C = 10\text{ mA}; V_{CE} = 10\text{ V}$	50	90	–	
		$I_C = 150\text{ mA}; V_{CE} = 10\text{ V}$	70	142	–	
		$I_C = 500\text{ mA}; V_{CE} = 10\text{ V}$	30	90	–	
		$I_C = 1\text{ A}; V_{CE} = 10\text{ V}$	15	50	–	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 1\text{ mA}$	–	150	200	mV
		$I_C = 150\text{ mA}; I_B = 15\text{ mA}$	–	150	350	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}$	–	0.35	1	V
		$I_C = 1\text{ A}; I_B = 100\text{ mA}$	–	0.66	1.6	V
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 1\text{ mA}$	–	0.69	1.2	V
		$I_C = 150\text{ mA}; I_B = 15\text{ mA}$	–	0.92	1.3	V
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}$	–	1.15	1.5	V
		$I_C = 1\text{ A}; I_B = 100\text{ mA}$	–	1.4	2	V
$C_c$	collector capacitance	$I_E = I_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	7	12	pF
$f_T$	transition frequency	$I_C = 50\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	50	185	–	MHz
<b>Switching Times (between 10% and 90% levels) see Fig.2</b>						
$t_{on}$	turn-on time	$I_{Con} = 150\text{ mA}; I_{Bon} = 15\text{ mA};$ $I_{Boff} = -15\text{ mA}$	–	55	–	ns
$t_d$	delay time		–	15	–	ns
$t_r$	rise time		–	40	–	ns
$t_{off}$	turn-off time		–	360	–	ns
$t_s$	storage time		–	300	–	ns
$t_f$	fall time		–	60	–	ns

## NPN switching transistor

BFX85



$V_i = 9.5 \text{ V}$ ;  $T = 500 \mu\text{s}$ ;  $t_p = 10 \mu\text{s}$ ;  $t_r = t_f \leq 3 \text{ ns}$ .  
 $R_1 = 68 \Omega$ ;  $R_2 = 325 \Omega$ ;  $R_B = 325 \Omega$ ;  $R_C = 160 \Omega$ .  
 $V_{BB} = -3.5 \text{ V}$ ;  $V_{CC} = 29.5 \text{ V}$ .  
 Oscilloscope: input impedance  $Z_i = 50 \Omega$ .

Fig.2 Test circuit for switching times.

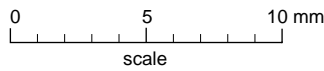
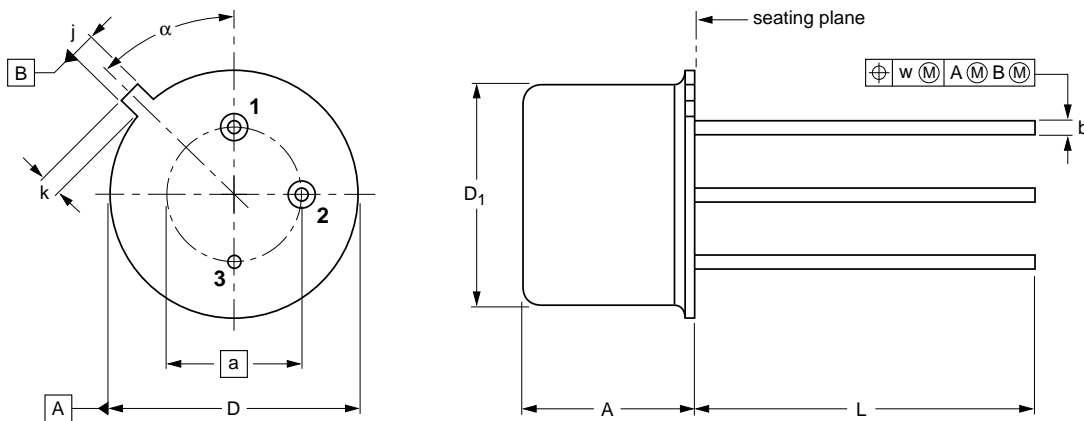
NPN switching transistor

BFX85

PACKAGE OUTLINE

Metal-can cylindrical single-ended package; 3 leads

SOT5/11



DIMENSIONS (mm are the original dimensions)

UNIT	A	a	b	D	D <sub>1</sub>	j	k	L	w	α
mm	6.60 6.35	5.08	0.48 0.41	9.39 9.08	8.33 8.18	0.85 0.75	0.95 0.75	14.2 12.7	0.2	45°

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT5/11		TO-39				97-04-11

## NPN switching transistor

BFX85

**DEFINITIONS**

<b>Data sheet status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	

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# Philips Semiconductors – a worldwide company

**Argentina:** see South America

**Australia:** 34 Waterloo Road, NORTH RYDE, NSW 2113,  
Tel. +61 2 9805 4455, Fax. +61 2 9805 4466

**Austria:** Computerstr. 6, A-1101 WIEN, P.O. Box 213,  
Tel. +43 1 60 101, Fax. +43 1 60 101 1210

**Belarus:** Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6,  
220050 MINSK, Tel. +375 172 200 733, Fax. +375 172 200 773

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**Bulgaria:** Philips Bulgaria Ltd., Energoproject, 15th floor,  
51 James Bourchier Blvd., 1407 SOFIA,  
Tel. +359 2 689 211, Fax. +359 2 689 102

**Canada:** PHILIPS SEMICONDUCTORS/COMPONENTS,  
Tel. +1 800 234 7381

**China/Hong Kong:** 501 Hong Kong Industrial Technology Centre,  
72 Tat Chee Avenue, Kowloon Tong, HONG KONG,  
Tel. +852 2319 7888, Fax. +852 2319 7700

**Colombia:** see South America

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**Denmark:** Prags Boulevard 80, PB 1919, DK-2300 COPENHAGEN S,  
Tel. +45 32 88 2636, Fax. +45 31 57 0044

**Finland:** Sinikalliontie 3, FIN-02630 ESPOO,  
Tel. +358 9 615800, Fax. +358 9 61580920

**France:** 4 Rue du Port-aux-Vins, BP317, 92156 SURESNES Cedex,  
Tel. +33 1 40 99 6161, Fax. +33 1 40 99 6427

**Germany:** Hammerbrookstraße 69, D-20097 HAMBURG,  
Tel. +49 40 23 53 60, Fax. +49 40 23 536 300

**Greece:** No. 15, 25th March Street, GR 17778 TAVROS/ATHENS,  
Tel. +30 1 4894 339/239, Fax. +30 1 4814 240

**Hungary:** see Austria

**India:** Philips INDIA Ltd, Shivsagar Estate, A Block, Dr. Annie Besant Rd.  
Worli, MUMBAI 400 018, Tel. +91 22 4938 541, Fax. +91 22 4938 722

**Indonesia:** see Singapore

**Ireland:** Newstead, Clonskeagh, DUBLIN 14,  
Tel. +353 1 7640 000, Fax. +353 1 7640 200

**Israel:** RAPAC Electronics, 7 Kehilat Saloniki St, PO Box 18053,  
TEL AVIV 61180, Tel. +972 3 645 0444, Fax. +972 3 649 1007

**Italy:** PHILIPS SEMICONDUCTORS, Piazza IV Novembre 3,  
20124 MILANO, Tel. +39 2 6752 2531, Fax. +39 2 6752 2557

**Japan:** Philips Bldg 13-37, Kohnan 2-chome, Minato-ku, TOKYO 108,  
Tel. +81 3 3740 5130, Fax. +81 3 3740 5077

**Korea:** Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL,  
Tel. +82 2 709 1412, Fax. +82 2 709 1415

**Malaysia:** No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR,  
Tel. +60 3 750 5214, Fax. +60 3 757 4880

**Mexico:** 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905,  
Tel. +9-5 800 234 7381

**Middle East:** see Italy

**Netherlands:** Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB,  
Tel. +31 40 27 82785, Fax. +31 40 27 88399

**New Zealand:** 2 Wagener Place, C.P.O. Box 1041, AUCKLAND,  
Tel. +64 9 849 4160, Fax. +64 9 849 7811

**Norway:** Box 1, Manglerud 0612, OSLO,  
Tel. +47 22 74 8000, Fax. +47 22 74 8341

**Philippines:** Philips Semiconductors Philippines Inc.,  
106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI,  
Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474

**Poland:** Ul. Lukiska 10, PL 04-123 WARSZAWA,  
Tel. +48 22 612 2831, Fax. +48 22 612 2327

**Portugal:** see Spain

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2092 JOHANNESBURG, P.O. Box 7430 Johannesburg 2000,  
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**South America:** Rua do Rocio 220, 5th floor, Suite 51,  
04552-903 São Paulo, SÃO PAULO - SP, Brazil,  
Tel. +55 11 821 2333, Fax. +55 11 829 1849

**Spain:** Balmes 22, 08007 BARCELONA,  
Tel. +34 3 301 6312, Fax. +34 3 301 4107

**Sweden:** Kottbygatan 7, Akalla, S-16485 STOCKHOLM,  
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**Switzerland:** Allmendstrasse 140, CH-8027 ZÜRICH,  
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**Taiwan:** Philips Semiconductors, 6F, No. 96, Chien Kuo N. Rd., Sec. 1,  
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**Turkey:** Talatpasa Cad. No. 5, 80640 GÜLTEPE/ISTANBUL,  
Tel. +90 212 279 2770, Fax. +90 212 282 6707

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252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461

**United Kingdom:** Philips Semiconductors Ltd., 276 Bath Road, Hayes,  
MIDDLESEX UB3 5BX, Tel. +44 181 730 5000, Fax. +44 181 754 8421

**United States:** 811 East Arques Avenue, SUNNYVALE, CA 94088-3409,  
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Printed in The Netherlands

117047/00/02/pp8

Date of release: 1997 Apr 22

Document order number: 9397 750 01957

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